

# SB07-03C

Shottky Barrier Diode

## 30V, 700mA Rectifier

## **Applications**

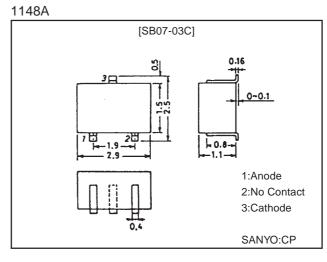
• High frequency rectification (switching regulators, converters, choppers).

### **Features**

- · Low forward voltage (V<sub>F</sub> max=0.55V).
- Fast reverse recorvery time (trr max=10ns).
- · Low switching noise.
- Low leakage current and high reliability due to highly reliable planar structure.

## **Package Dimensions**

unit:mm



## **Specifications**

### Absolute Maximum Ratings at Ta = 25°C

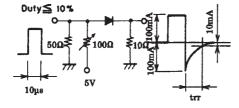
Parameter	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>		30	V
Nonrepetitive Peak Reverse Surge Voltage	V <sub>RSM</sub>		35	V
Average Output Current	IO		700	mA
Surge Forward Current	IFSM	50Hz sine wave, 1cycle	5	А
Junction Temperature	Tj		-55 to +125	°C
Storage Temperature	Tstg		-55 to +125	°C

#### **Electrical Characteristics at Ta = 25°C**

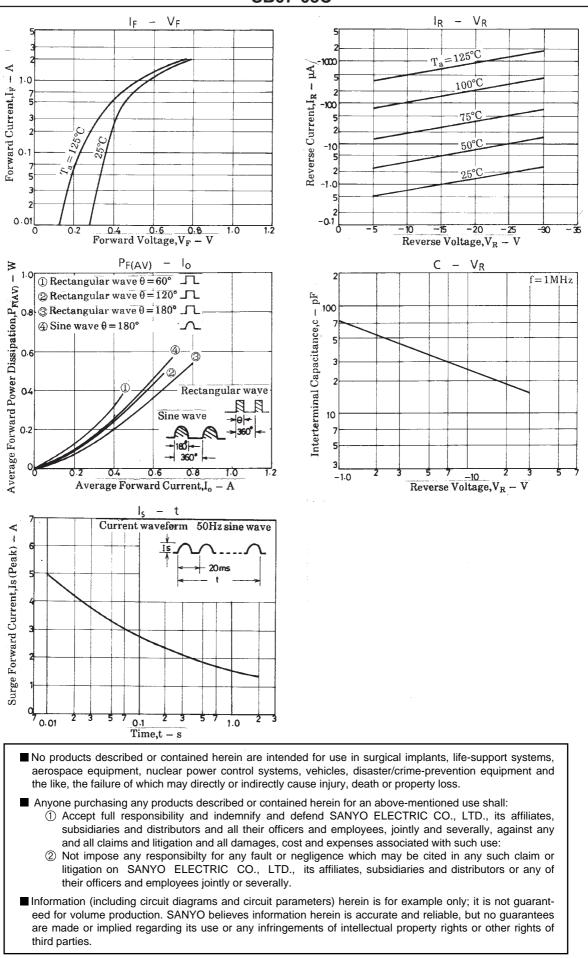
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Reverse Voltage	VR	I <sub>R</sub> =300μA	30			V
Forward Voltage	VF	I <sub>F</sub> =700mA			0.55	V
Reverse Current	۱ <sub>R</sub>	V <sub>R</sub> =15V			80	μΑ
Interterminal Capacitance	С	V <sub>R</sub> =10V, f=1MHz		25		pF
Reverse Recorvery Time	trr	I <sub>F</sub> =I <sub>R</sub> =100mA, See specified Test Circuit			10	ns
Thermal Resistance	Rthj-a(1)			420		°C/W
	Rthj-a(2)	Mounted on Cu-foild area of 16mm <sup>2</sup> ×0.2mm on glass epoxy board		330		°C/W

· Marking:J

#### trr Test Circuit



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This catalog provides information as of March, 1998. Specifications and information herein are subject to change without notice.